## Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

(Currently Amended) A semiconductor device comprising: 1. a substrate; and an electrode-electrode, the electrode being formed on the substrate; substrate; wherein-a through-hole is-being formed through the electrode and the substrate in a stacking direction of the electrode and the substrate, substrate; a conductive member being inserted into the through-hole; through-hole; wherein an insulating material is, being disposed between the electrode and the conductive member, the insulating material including a wall portion located higher than at least the electrode; and electrode; and at least an interlayer dielectric being formed between the substrate and the electrode, the through-hole being formed in the interlayer dielectric, and surfaces of the interlayer dielectric and substrate in the through-hole being formed to have a level difference in a boundary area between the substrate and the interlayer dielectric,

wherein the conductive member is being formed over the wall portion of the insulating material from the through-hole and is-being connected with the electrode.

(Original) The semiconductor device as defined in claim 1, wherein the insulating material is formed to cover an upper surface of the electrode and a surface in the through-hole, and includes a connection hole for connecting at least the electrode with the conductive member at a position differing from the through-hole, the wall portion being disposed between the connection hole and the through-hole.

3-4. (Canceled)

2.

(Original) The semiconductor device as defined in claim 1, 5.

wherein the conductive member functions as a connection terminal which secures electrical connection in an axial direction of the through-hole.

- 6. (Original) The semiconductor device as defined in claim 1,
  wherein a part of the conductive member projects outward from the throughhole on a side of the substrate opposite to a side on which the electrode is formed.
- 7. (Original) A semiconductor device comprising a plurality of the semiconductor devices as defined in claim 1 which are stacked, each of the semiconductor devices being electrically connected through the conductive members.
- 8. (Original) A circuit board comprising the semiconductor device as defined in claim 1.
- 9. (Original) An electronic instrument comprising the circuit board as defined in claim 8.
  - 10-15. (Canceled)